## BAV99L, SBAV99L

## Dual Series Switching Diode

## Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (Each Diode)

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 100 | Vdc |
| Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 215 | mAdc |
| Peak Forward Surge Current | $\mathrm{I}_{\text {FM(surge) }}$ | 500 | mAdc |
| Repetitive Peak Reverse Voltage | $\mathrm{V}_{\text {RRM }}$ | 100 | V |
| Average Rectified Forward Current (Note 1) | $\mathrm{I}_{\mathrm{F}(\mathrm{AV})}$ | 715 | mA |
| (averaged over any 20 ms period) |  |  |  |
| Repetitive Peak Forward Current | $\mathrm{I}_{\text {FRM }}$ | 450 | mA |
| Non-Repetitive Peak Forward Current | $\mathrm{I}_{\mathrm{FSM}}$ |  | A |
| $\mathrm{t}=1.0$ us |  | 2.0 |  |
| $\mathrm{t}=1.0 \mathrm{~ms}$ |  |  |  |
| $\mathrm{t}=1.0 \mathrm{~s}$ |  | 1.0 |  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Total Device Dissipation <br> FR-5 Board (Note 1) $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 225 | mW |
| Thermal Resistance, Junction-to-Ambient | $\mathrm{R}_{\text {日JA }}$ | 556 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Total Device Dissipation <br> Alumina Substrate (Note 2) <br> $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 300 | mW |
| Thermal Resistance, Junction-to-Ambient |  | $\mathrm{R}_{\text {日JA }}$ | 417 |
| Junction and Storage | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -65 to <br> +150 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Temperature Range |  |  |  |

1. $\mathrm{FR}-5=1.0 \times 0.75 \times 0.062 \mathrm{in}$.
2. Alumina $=0.4 \times 0.3 \times 0.024$ in $99.5 \%$ alumina.

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CASE 318
SOT-23 STYLE 11
CATHODE/ANODE

## MARKING DIAGRAM



A7 = Device Code
$\mathrm{M}=$ Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| BAV99LT1G | SOT-23 <br> (Pb-Free) | $3,000 /$ Tape \& Reel |
| SBAV99LT1G | SOT-23 <br> (Pb-Free) | $3,000 /$ Tape \& Reel |
| BAV99LT3G | SOT-23 <br> (Pb-Free) | $10,000 /$ Tape \& Reel |
| SBAV99LT3G | SOT-23 <br> (Pb-Free) | $10,000 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAV99L, SBAV99L

OFF CHARACTERISTICS $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted) (Each Diode)

| Characteristic | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Reverse Breakdown Voltage, $\left(\mathrm{l}_{(\mathrm{BR})}=100 \mu \mathrm{~A}\right)$ | $\mathrm{V}_{\text {(BR) }}$ | 100 | - | Vdc |
| $\begin{aligned} & \text { Reverse Voltage Leakage Current, } \\ & \left(V_{R}=100 \mathrm{Vdc}\right) \\ & \left(V_{R}=25 \mathrm{Vdc}, T_{J}=150^{\circ} \mathrm{C}\right) \\ & \left(\mathrm{V}_{\mathrm{R}}=70 \mathrm{Vdc}, \mathrm{~T}_{J}=150^{\circ} \mathrm{C}\right) \end{aligned}$ | $I_{\text {R }}$ | - | $\begin{aligned} & 1.0 \\ & 30 \\ & 50 \end{aligned}$ | $\mu \mathrm{Adc}$ |
| Diode Capacitance, $\left(V_{R}=0, f=1.0 \mathrm{MHz}\right)$ | $C_{D}$ | - | 1.5 | pF |
| Forward Voltage, $\begin{aligned} & \left(I_{F}=1.0 \mathrm{mAdc}\right) \\ & \left(I_{F}=10 \mathrm{mAdc}\right) \\ & \left(I_{F}=50 \mathrm{mAdc}\right) \\ & \left(I_{F}=150 \mathrm{mAdc}\right) \end{aligned}$ | $V_{F}$ | - | $\begin{aligned} & 715 \\ & 855 \\ & 1000 \\ & 1250 \end{aligned}$ | mVdc |
| Reverse Recovery Time, $\left(I_{F}=I_{R}=10 \mathrm{mAdc}, \mathrm{i}_{\mathrm{R}(\mathrm{REC})}=1.0 \mathrm{mAdc}\right) \mathrm{R}_{\mathrm{L}}=100 \Omega$ | $\mathrm{t}_{\mathrm{rr}}$ | - | 6.0 | ns |
| Forward Recovery Voltage, $\left(\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{t}_{\mathrm{r}}=20 \mathrm{~ns}\right)$ | $V_{\text {FR }}$ | - | 1.75 | V |

## CURVES APPLICABLE TO EACH DIODE




Figure 3. Capacitance


SOT-23 (TO-236)
CASE 318-08
ISSUE AS
DATE 30 JAN 2018

## SCALE 4:1



NOTES:
IMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

|  | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| $\mathbf{c}$ | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| $\mathbf{H E}_{\mathbf{E}}$ | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | $0^{\circ}$ | --- | $10^{\circ}$ | $0^{\circ}$ | --- | $10^{\circ}$ |

GENERIC
MARKING DIAGRAM*

RECOMMENDED SOLDERING FOOTPRINT


DIMENSIONS: MILLIMETERS


XXX = Specific Device Code
M = Date Code

- = Pb-Free Package
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " $\quad$ ", may or may not be present.


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